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(54) Title: PROCESS FOR PRODUCING A HEAT RESISTANT RELIEF STRUCTURE

(57) Abstract: A process for producing a heat resistant relief structure on a substrate, the process comprising the steps of: (a) providing a substrate; (b) in a first coating step, coating the substrate with a composition comprising a polyamic acid and *gamma*-butyrolactone to form a layer of polyamic acid having a thickness of at least about 0.5 umicro;m; (c) baking the layer of polyamic acid at a temperature or temperatures below 140 °C; (d) in a second coating step, coating a layer of a photoresist over the layer of polyamic acid to form a bilayer coating; (e) exposing the bilayer coating to radiation <250 nm (f) developing the bilayer coating with one or more aqueous tetramethyl ammonium hydroxide developers; (g) removing the remaining photoresist layer; and (h) curing the polyamic acid layer at a temperature at least about 200 °C to produce a polyimide structure wherein the polyamic acid is soluble in aqueous tetramethyl ammonium hydroxide and insoluble in a solvent used with the photoresist.



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